



CPH3456 — N-Channel Silicon MOSFET

General-Purpose Switching Device Applications

Features

- ON-resistance $R_{DS(on)1}=54m\Omega$ (typ.)
- 1.8V drive
- Halogen free compliance

Specifications

Absolute Maximum Ratings at $T_a=25^\circ C$

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		20	V
Gate-to-Source Voltage	V_{GSS}		± 12	V
Drain Current (DC)	I_D		3.5	A
Drain Current (Pulse)	I_{DP}	$PW \leq 10\mu s$, duty cycle $\leq 1\%$	14	A
Allowable Power Dissipation	P_D	When mounted on ceramic substrate (900mm ² ×0.8mm)	1.0	W
Channel Temperature	T_{ch}		150	°C
Storage Temperature	T_{stg}		-55 to +150	°C

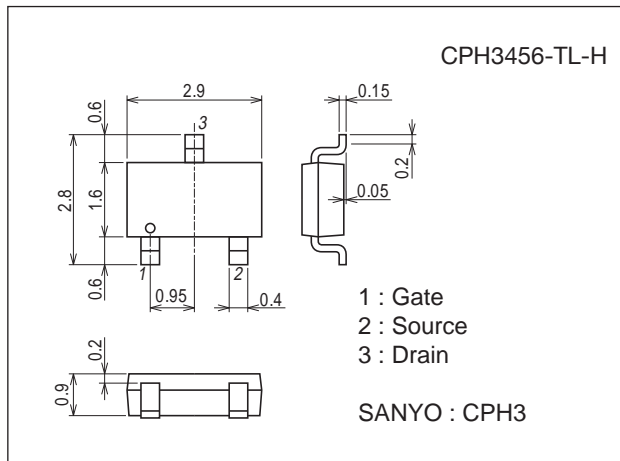
This product is designed to "ESD immunity < 200V**", so please take care when handling.

* Machine Model

Package Dimensions

unit : mm (typ)

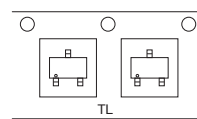
7015A-004



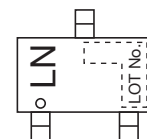
Product & Package Information

- Package : CPH3
- JEITA, JEDEC : SC-59, TO-236, SOT-23
- Minimum Packing Quantity : 3,000 pcs./reel

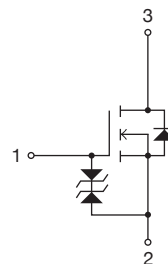
Packing Type: TL



Marking



Electrical Connection

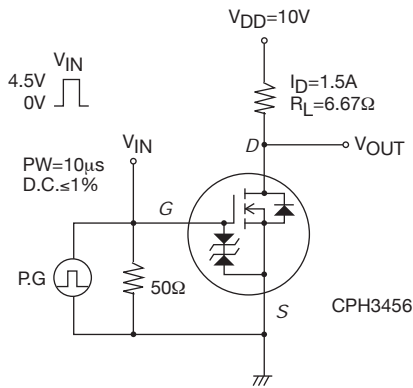


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Electrical Characteristics at Ta=25°C

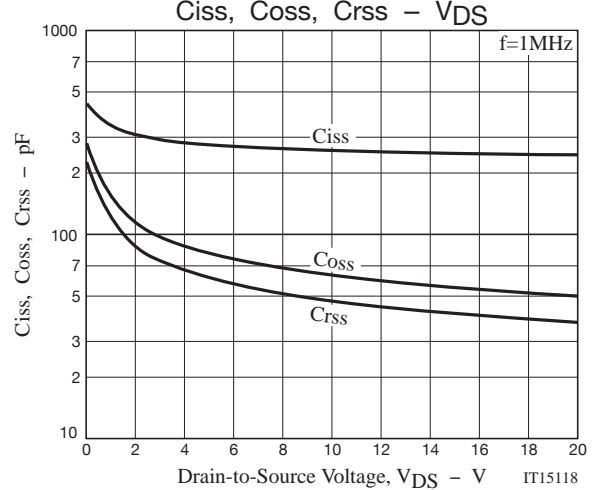
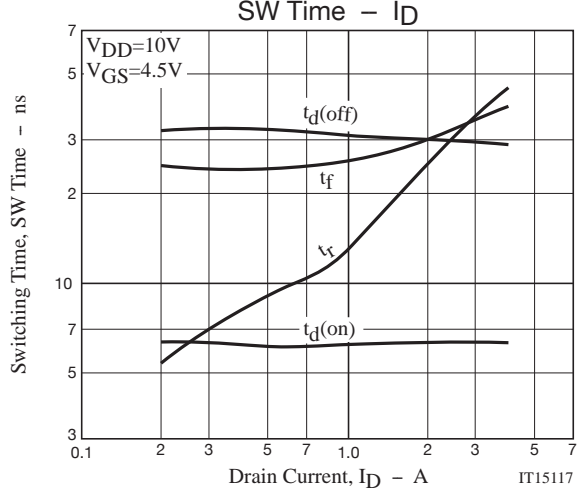
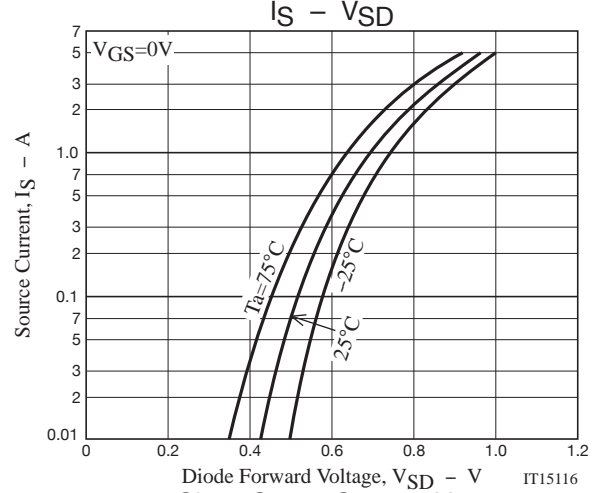
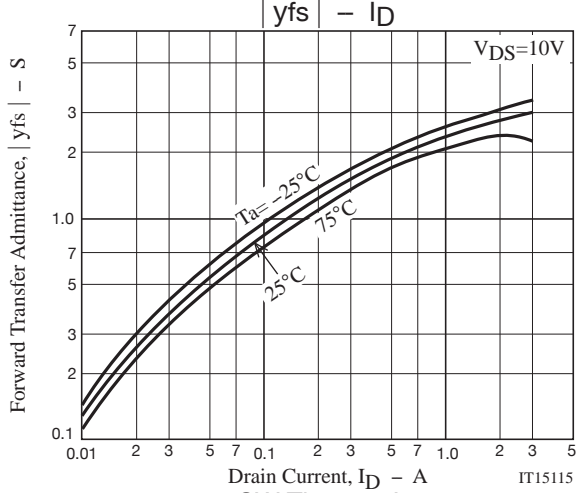
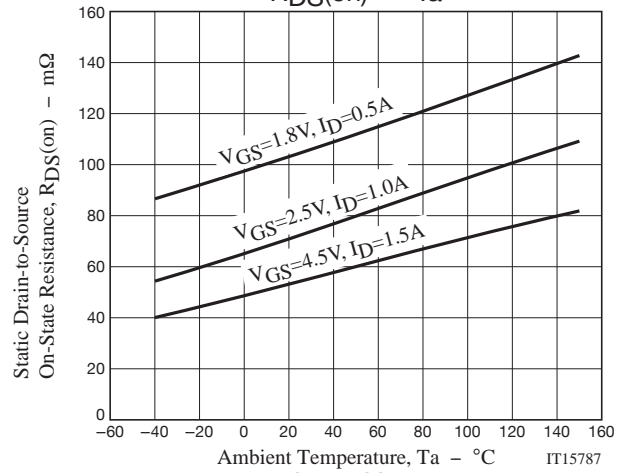
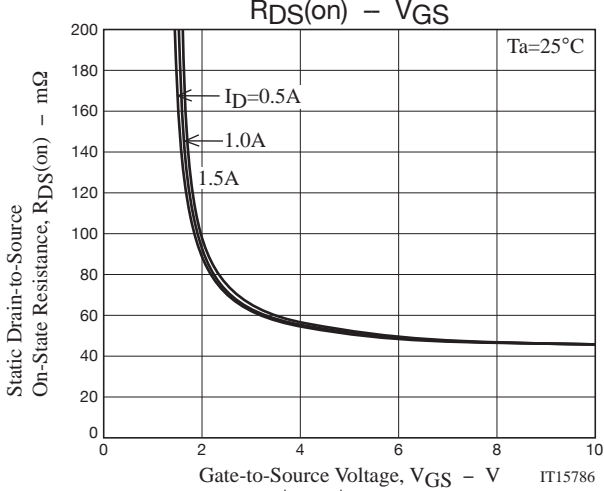
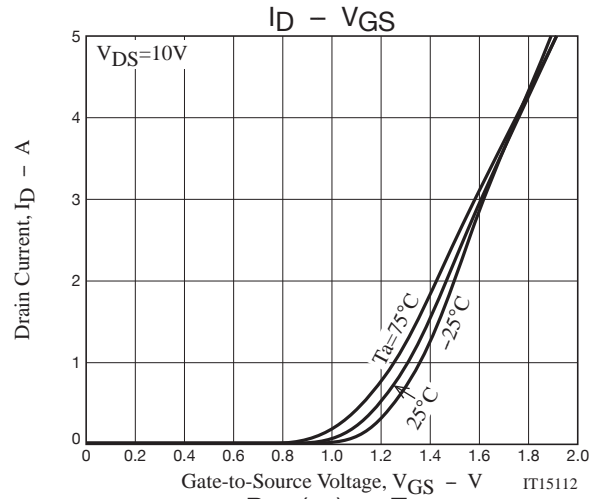
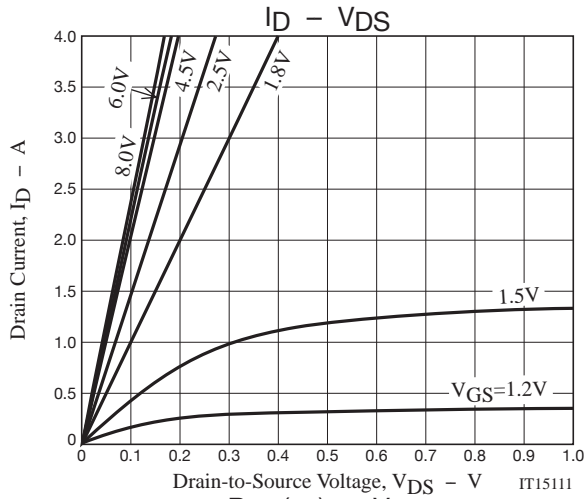
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR)DSS	I _D =1mA, V _{GS} =0V	20			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =20V, V _{GS} =0V			1	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±8V, V _{DS} =0V			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} =10V, I _D =1mA	0.4		1.3	V
Forward Transfer Admittance	y _{fs}	V _{DS} =10V, I _D =1.5A		2.8		S
Static Drain-to-Source On-State Resistance	R _{DS(on)1}	I _D =1.5A, V _{GS} =4.5V		54	71	mΩ
	R _{DS(on)2}	I _D =1A, V _{GS} =2.5V		73	103	mΩ
	R _{DS(on)2}	I _D =0.5A, V _{GS} =1.8V		104	156	mΩ
Input Capacitance	C _{iss}	V _{DS} =10V, f=1MHz		260		pF
Output Capacitance	C _{oss}	V _{DS} =10V, f=1MHz		65		pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} =10V, f=1MHz		50		pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit.		6.2		ns
Rise Time	t _r	See specified Test Circuit.		19		ns
Turn-OFF Delay Time	t _{d(off)}	See specified Test Circuit.		30		ns
Fall Time	t _f	See specified Test Circuit.		28		ns
Total Gate Charge	Q _g	V _{DS} =10V, V _{GS} =4.5V, I _D =3.5A		2.8		nC
Gate-to-Source Charge	Q _{gs}	V _{DS} =10V, V _{GS} =4.5V, I _D =3.5A		0.6		nC
Gate-to-Drain "Miller" Charge	Q _{gd}	V _{DS} =10V, V _{GS} =4.5V, I _D =3.5A		0.9		nC
Diode Forward Voltage	V _{SD}	I _S =3.5A, V _{GS} =0V		0.85	1.2	V

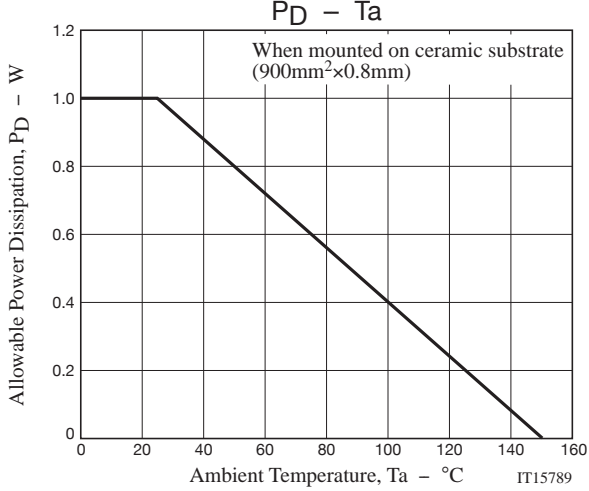
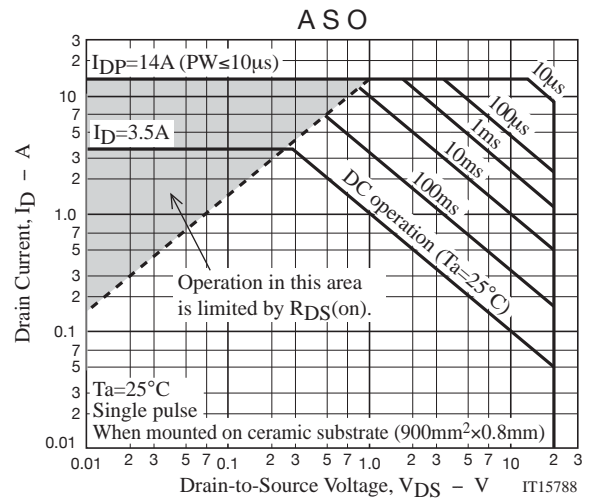
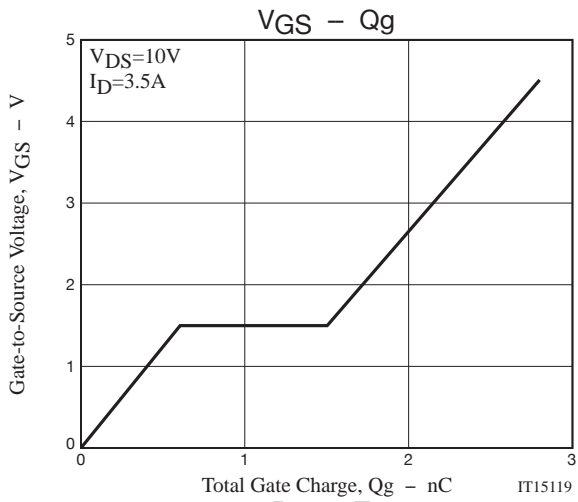
Switching Time Test Circuit



Ordering Information

Device	Package	Shipping	memo
CPH3456-TL-H	CPH3	3,000pcs./reel	Pb Free and Halogen Free



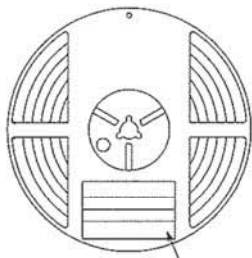


Embossed Taping Specification
CPH3456-TL-H

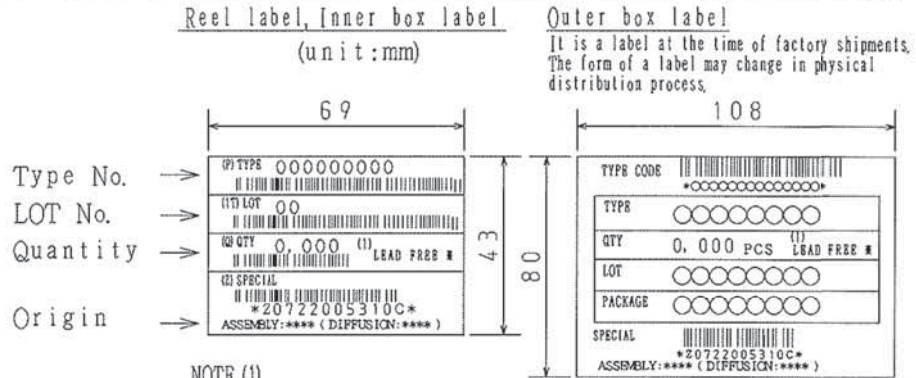
1. Packing Format

Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
CPH3	CPH3	3,000	15,000	90,000	5 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210

Packing method



Reel label



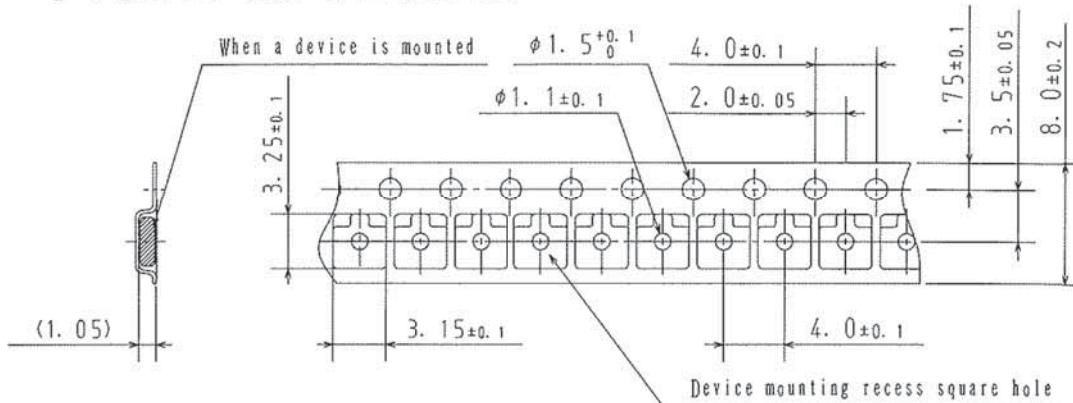
NOTE (1)

The LEAD FREE # description shows that the surface treatment of the terminal is lead free.

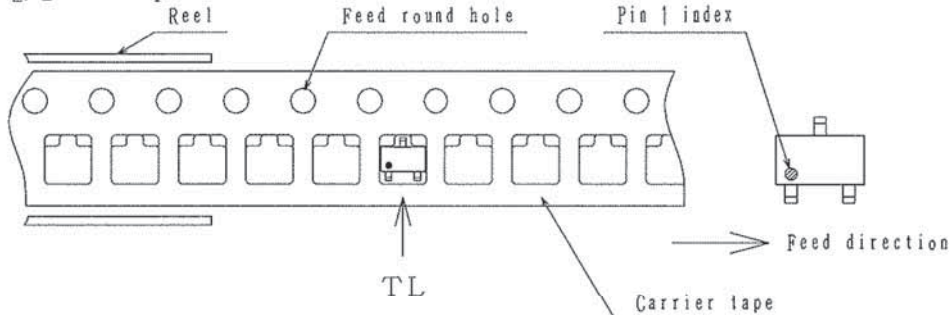
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



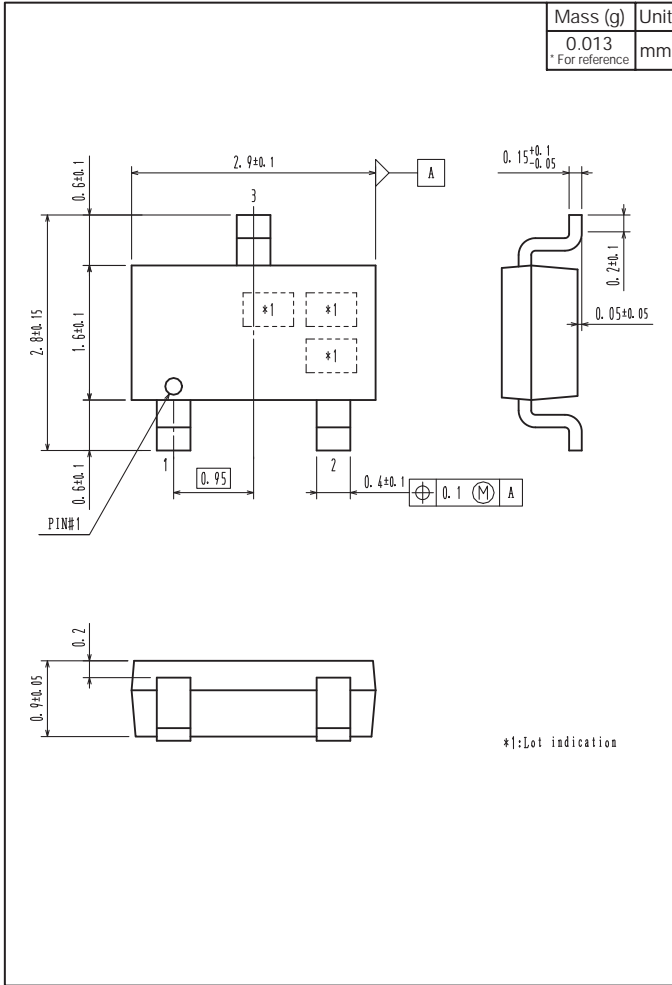
2-2. Device placement direction



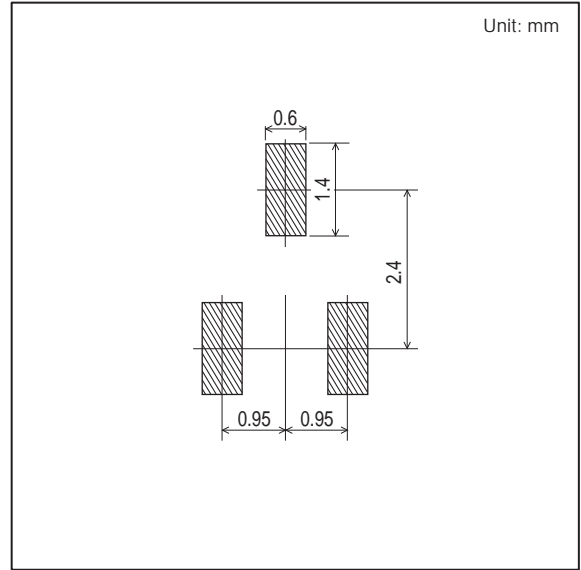
Those with one electrode terminal on the feed hole side.....TL

CPH3456

Outline Drawing CPH3456-TL-H



Land Pattern Example



Note on usage : Since the CPH3456 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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